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(54) INSULATED GATE TYPE SEMICONDUCTOR DEVICE AND FABRICATION THEREOF

(57) Abstract:

PROBLEM TO BE SOLVED: To improve SOA of an insulated gate type semiconductor device by making difficult for a parasitic transistor of an insulated gate type semiconductor device to turn ON.

SOLUTION: A parasitic bipolar transistor formed of N^+ emitter region, P base layer and N^- layer is set difficult to turn ON by providing P^+ semiconductor layer 45 having impurity concentration higher than that of the N' emitter region 44 in such a manner that it overlaps with the end part adjacent to the N^+ emitter region 44 of U type IGBT and in contact with the P base region 43 at the bottom part.